DATA SHEET

PHE13007
Silicon Diffused Power Transistor

Product specification

February 2018

WeEn
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Silicon Diffused Power Transistor PHE13007

GENERAL DESCRIPTION

The PHE13007 is a silicon npn power switching transistor in the TO220AB envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

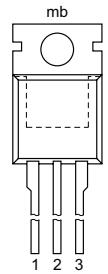
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	700	V
V_{CBO}	Collector-Base voltage (open emitter)		-	700	V
V_{CEO}	Collector-emitter voltage (open base)		-	400	V
V_{EBO}	Emitter-Base voltage (I_B = 0)		-	9	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	16	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	80	W
V_{CEsat}	Collector-emitter saturation voltage	I_C = 5.0 A;I_B = 1.0 A	0.35	2.0	V
t_f	Fall time	I_C = 5 A; I_{B1} = 1 A	40	120	ns

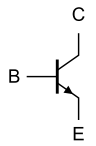
PINNING - TO220AB

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

PIN CONFIGURATION



SYMBOL



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LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector to emitter voltage	V_{BE} = 0 V	-	700	V
V_{CEO}	Collector to emitter voltage (open base)		-	400	V
V_{CBO}	Collector to base voltage (open emitter)		-	700	V
V_{EBO}	Emitter-Base voltage (I_B = 0)		-	9	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	16	A
I_B	Base current (DC)		-	4	A
I_{BM}	Base current peak value		-	8	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	80	W
T_{stg}	Storage temperature		-65	150	˚C
T_j	Junction temperature		-	150	˚C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Junction to mounting base		-	1.56	K/W
$R_{th\ j\text{-}a}$	Junction to ambient	in free air	60	-	K/W

STATIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	Collector cut-off current [1]	V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$	-	-	0.2	mA
I_{CES}		V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$; T_j = 125 ˚C	-	-	1.0	mA
I_{EBO}	Emitter cut-off current	V_{EB} = 9 V; I_C = 0 A	-	-	1.0	mA
$V_{CEOsust}$	Collector-emitter sustaining voltage	I_B = 0 A; I_C = 10 mA; L = 25 mH	400	-	-	V
V_{CEsat}	Collector-emitter saturation voltage	I_C = 2.0 A;I_B = 0.4 A	-	0.15	1.0	V
V_{CEsat}		I_C = 5.0 A;I_B = 1.0 A	-	0.35	2.0	V
V_{CEsat}		I_C = 5.0 A;I_B = 1.0 A (T_C = 100˚C)	-	0.51	3.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C = 2.0 A;I_B = 0.4 A	-	0.92	1.2	V
V_{BEsat}		I_C = 5.0 A;I_B = 1.0 A	-	1.05	1.6	V
V_{BEsat}		I_C = 5.0 A;I_B = 1.0 A (T_C = 100˚C)	-	1.00	1.5	V
h_{FE}	DC current gain	I_C = 2.0 A; V_{CE} = 5 V	8	17	40	
h_{FEsat}		I_C = 5.0 A; V_{CE} = 5 V	5	9	30	

DYNAMIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	I_{Con} = 5 A; I_{Bon} = -I_{Boff} = 1 A; R_L = 75 ohms; V_{BB2} = 4 V;			
t_s	Turn-off storage time		1.8	3.0	µs
t_f	Turn-off fall time		0.3	0.7	µs
	Switching times (inductive load)	I_{Con} = 5 A; I_{Bon} = 1 A; L_B = 1 µH; -V_{BB} = 5 V			
t_s	Turn-off storage time		1.2	2.0	µs
t_f	Turn-off fall time		40	120	ns
	Switching times (inductive load)	I_{Con} = 5 A; I_{Bon} = 1 A; L_B = 1 µH; -V_{BB} = 5 V; T_j = 100 ˚C			
t_s	Turn-off storage time		1.6	3.0	µs
t_f	Turn-off fall time		100	200	ns

1 Measured with half sine-wave voltage (curve tracer).

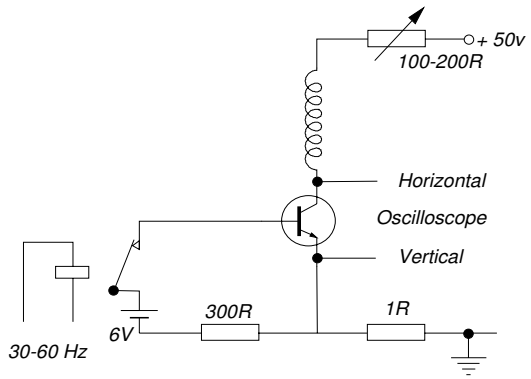


Fig.1. Test circuit for $V_{CEOsust}$.

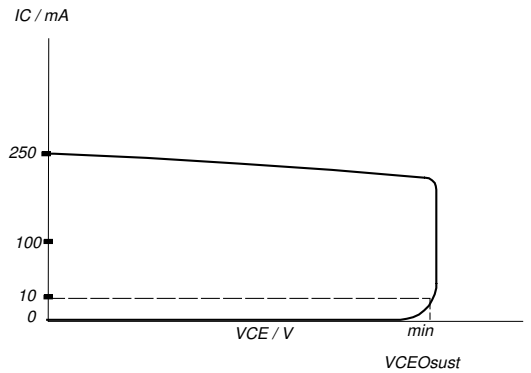


Fig.2. Oscilloscope display for $V_{CEOsust}$.

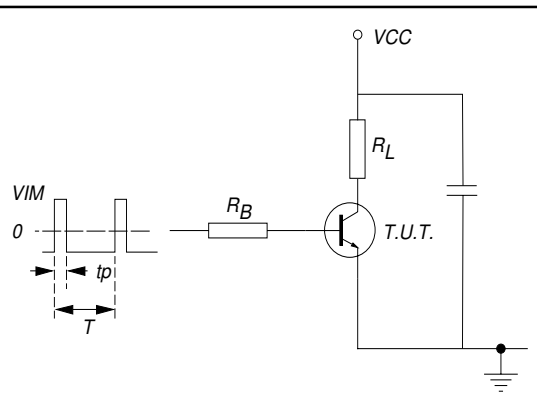


Fig.3. Test circuit resistive load. V_{IM} = -6 to +8 V
V_{CC} = 250 V; t_p = 20 μs; δ = t_p / T = 0.01.
R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

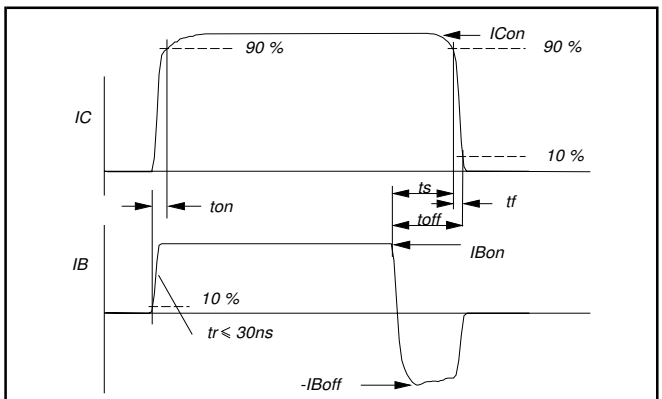


Fig.4. Switching times waveforms with resistive load.

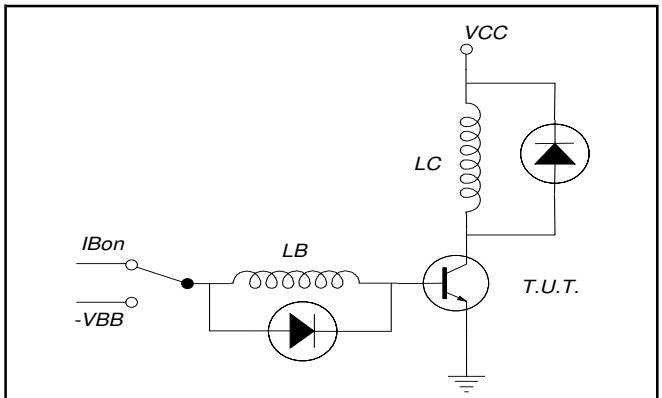


Fig.5. Test circuit inductive load.
V_{CC} = 300 V; -V_{BE} = 5 V; L_C = 200 uH; L_B = 1 uH

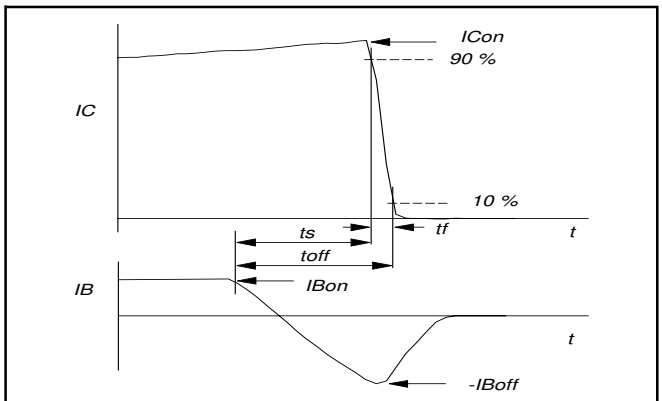


Fig.6. Switching times waveforms with inductive load.

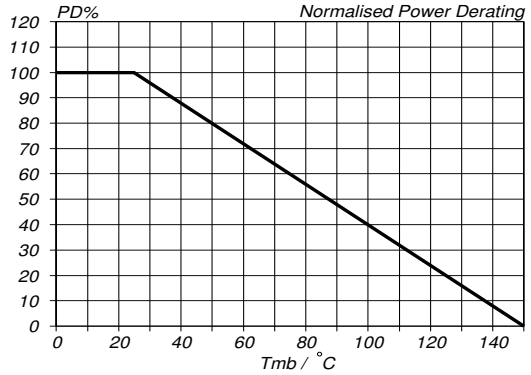


Fig.7. Normalised power dissipation. PD% = 100·PD/PD $_{25°C}$ = f (T_{mb})

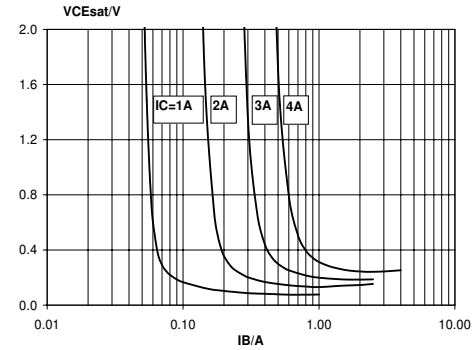


Fig.10. Collector-Emitter saturation voltage. Solid lines = typ values, V_{CEsat} = f(IB); T_j=25˚C.

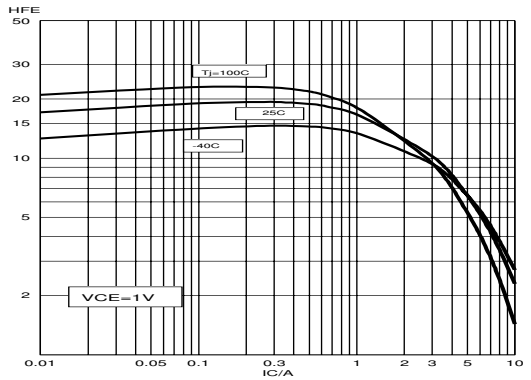


Fig.8. Typical DC current gain. h_{FE} = f(I_C) parameter V_{CE}

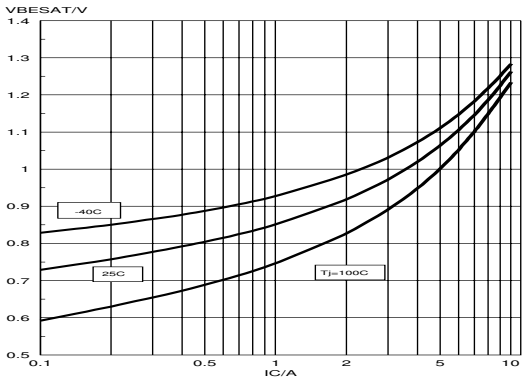


Fig.11. Base-Emitter saturation voltage. Solid lines = typ values, V_{BEsat} = f(IC); at IC/IB =4.

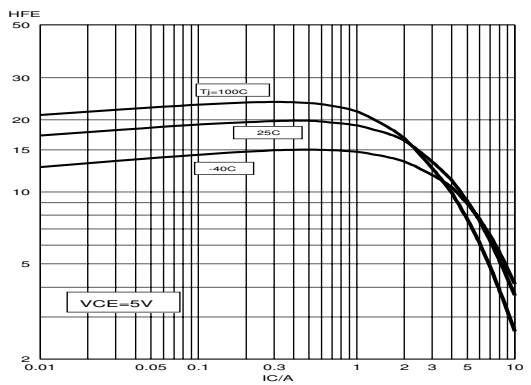


Fig.9. Typical DC current gain. h_{FE} = f(I_C) parameter V_{CE}

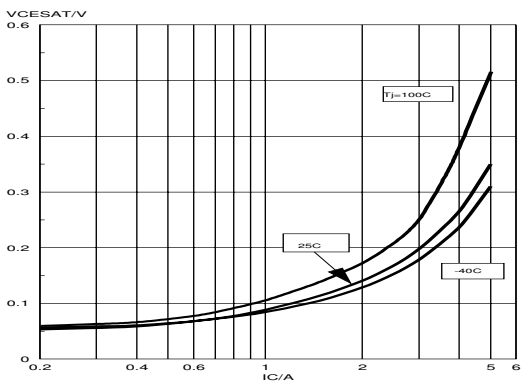


Fig.12. Collector-Emitter saturation voltage. Solid lines = typ values, V_{CEsat} = f(IC); at IC/IB =4.

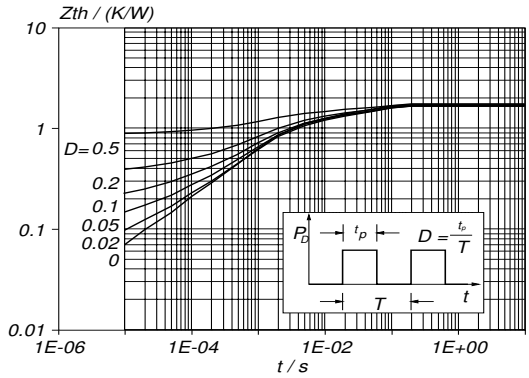


Fig.13. Transient thermal impedance. $Z_{th\ j\text{-}mb} = f(t)$; parameter $D = t_p/T$

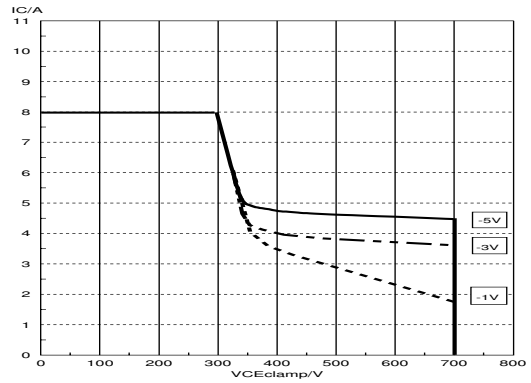


Fig.15. Reverse bias safe operating area ($T_j < T_{jmax}$) for $-V_{BE}$ = 5V,3V & 1V.

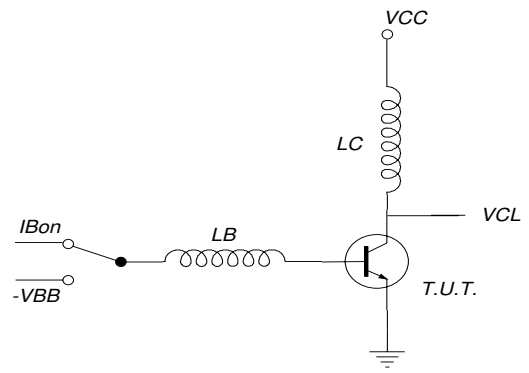
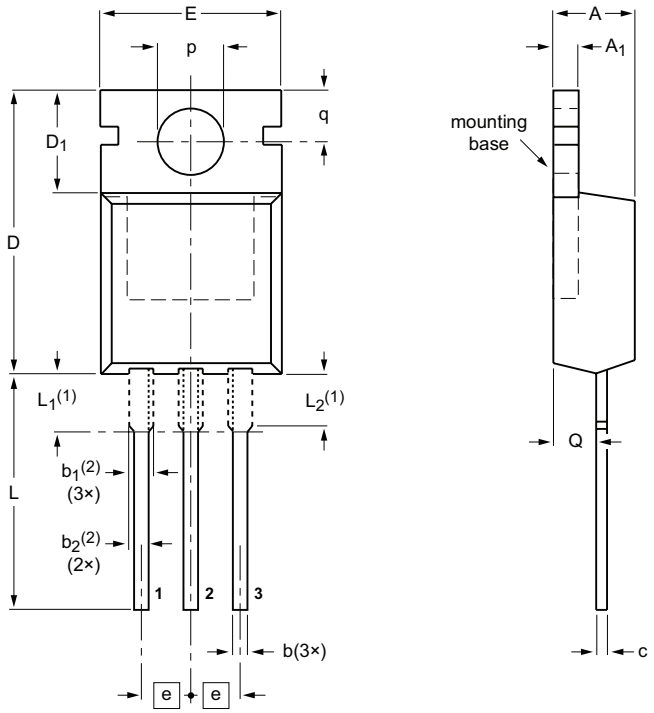


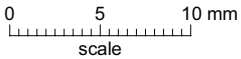
Fig.14. Test circuit for reverse bias safe operating area.

V_{clamp} < 700V; V_{cc} = 150V; $-V_{be}$ = 5V,3V & 1V; L_B = 1µH; L_C = 200µH.

MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**





DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1(2)	b_2(2)	c	D	D_1	E	e	L	L_1(1)	L_2(1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes
1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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